(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
26 October 2023 (26.10.2023)

WIPO | PCT

(10) International Publication Number
WO 2023/202936 A1

(51) International Patent Classification:
H01L 21/02 (2006.01)

(21) International Application Number:
PCT/EP2023/059604

(22) International Filing Date:
13 April 2023 (13.04.2023)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2022-068464 18 April 2022 (18.04.2022) JP

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CV, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IQ, IR, IS, IT, JM, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, MG, MK, MN, MU, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, WS, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, CV, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SC, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, ME, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Published:
— *with international search report (Art. 21(3))*

(54) Title: METHOD FOR MANUFACTURING SILICON NITROGENOUS FILM ON SUBSTRATE HAVING A GROOVE

(57) Abstract: A method for manufacturing a silicon nitrogenous film on a substrate having a groove comprising the following steps: (a) applying a silicon nitrogenous composition on a substrate having a groove to form a composition layer; (b) irradiating the composition layer with light having a wavelength of 200 to 229 nm; and (c) heating the substrate in a non-oxidizing atmosphere, wherein the refractive index of the silicon nitrogenous film is 1.70 to 2.40 for the light having a wavelength of 633 nm.

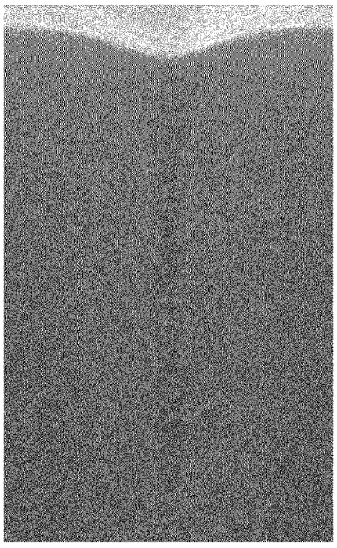


Figure 1

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